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Go to: Derwent

⊠ i

愛Title:

JP10082707A2: PRESSURE DETECTOR

P Derwent Title:

Pressure detector using sensor chip as sensor element or strain gauge has passive-state film formed on gas-contact face of diaphragm of pressure detector using sensor chip to prevent corrosion, or water content emission from, or catalytic action at gas-contact face [Derwent Record]

PCountry:

JP Japan

VKind:

A (See also: JP03403294B2)

PInventor:

OMI TADAHIRO: DOI RYOSUKE: **NISHINO KOJI**; **IKEDA SHINICHI**;

PAssignee:

OMI TADAHIRO FUJIKIN:KK

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Published / Filed:

1998-03-31 / 1996-09-10

PApplication

Number:

JP1996000238706

₱IPC Code:

G01L 9/04; G01L 19/00; G01L 19/06;

Priority Number:

1996-09-10 JP1996000238706

PAbstract:

PROBLEM TO BE SOLVED: To eliminate the possibility of lowering the quality of product even a pressure detector is applied to a semiconductor production process, by forming a passive film on the gas-contact face of a stainless steel diaphragm having specified dimensions provided on a diaphraqm base.

SOLUTION: A diaphragm 3 of about 50µm thick having an inside diameter of about 10mm is made of stainless steel and has a gascontact face 3a on which a passive film 3b of chromium oxide, a fluorinated passive film 3b or a mixed oxide passive film 3b of aluminum oxide and chromium oxide is formed. After forming the diaphragm 3 integrally with a diaphragm base 4, the diaphragm base 4 formed with the passive film 3b and a sensor base 1 are abutted against the gas contact face 3a of the diaphragm 3 and the

entire circumference of the side wall face is welded 8. Subsequently, an oil injection hole 1b is filled with a pressure transmission medium (silicon oil) 5 and a sealing body (ball) 6 is welded 10 to the sensor base 1 thus sealing the silicon oil 5

hermetically.

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None

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Legal Status: P Designated

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영Family:

Show 16 known family members

8 Other Abstract

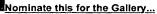
None













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FUJIKIN:KK

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OMI TADAHIRO

DOI RYOSUKE NISHINO KOJI

IKEDA SHINICHI

(54) PRESSURE DETECTOR

(57) Abstract:

PROBLEM TO BE SOLVED: To eliminate the possibility of lowering the quality of product even a pressure detector is applied to a semiconductor production process, by forming a passive film on the gas-contact face of a stainless steel diaphragm having specified dimensions provided on a diaphragm base.

SOLUTION: A diaphragm 3 of about 50 µm thick having an inside diameter of about 10mm is made of stainless steel and has a gas-contact face 3a on which a passive film 3b of chromium oxide, a fluorinated passive film 3b or a mixed oxide passive film 3b of aluminum oxide and chromium oxide is formed. After forming the diaphragm 3 integrally with a diaphragm base 4, the diaphragm base 4 formed with the passive film 3b and a sensor base 1 are abutted against the gas contact face 3a of the diaphragm 3 and the entire circumference of the side wall face is welded 8. Subsequently, an oil injection hole 1b is filled with a pressure transmission medium (silicon oil) 5 and a sealing body (ball) 6 is welded 10 to the sensor base 1 thus sealing the silicon oil 5 hermetically.

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